




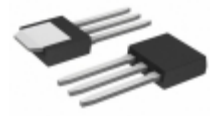
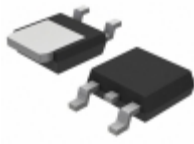
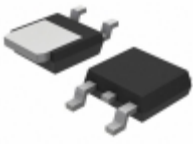
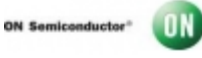
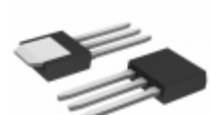
	<h2 style="color: red;">NTD3808NT4G</h2>
	<p>Hersteller-Teilenummer: NTD3808NT4G</p> <p>Hersteller / Marke: AMI Semiconductor / ON Semiconductor</p> <p>Teil der Beschreibung: MOSFET N-CH 16V 12A DPAK</p> <p>Datenblätter:  NTD3808NT4G.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 10000 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
	
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	NTD3808NT4G
Hersteller	AMI Semiconductor / ON Semiconductor
Beschreibung	MOSFET N-CH 16V 12A DPAK
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	10000 pcs Stock
Serie	-
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 175°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	TO-252-3, DPak (2 Leads + Tab), SC-63
Supplier Device-Gehäuse	DPAK
Verlustleistung (max)	1.3W (Ta), 52W (Tc)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	16V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	12A (Ta), 76A (Tc)
Rds On (Max) @ Id, Vgs	5.8 mOhm @ 15A, 10V
VGS (th) (Max) @ Id	2.5V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	21nC @ 4.5V
Eingabekapazität (Ciss) (Max) @ Vds	1660pF @ 12V
Verpackung	Tape & Reel (TR)

NTD3808NT4G ist neu im Original, Suche NTD3808NT4G Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie NTD3808NT4G AMI Semiconductor / ON Semiconductor mit Garantie und Vertrauen. Anfrage NTD3808NT4G: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>NTD3817N-35G AMI Semiconductor / ON Semiconductor MOSFET N-CH 16V 7.6A IPAK</p>	 <p>NTD3813NT4G AMI Semiconductor / ON Semiconductor MOSFET N-CH 16V 9.6A DPAK</p>	 <p>NTD3813N-35G AMI Semiconductor / ON Semiconductor MOSFET N-CH 16V 9.6A IPAK</p>	 <p>NTD3813N-1G AMI Semiconductor / ON Semiconductor MOSFET N-CH 16V 9.6A IPAK</p>
 <p>NTD32N06T4G AMI Semiconductor / ON Semiconductor MOSFET N-CH 60V 32A DPAK</p>	 <p>NTD32N06LT4G AMI Semiconductor / ON Semiconductor MOSFET N-CH 60V 32A DPAK</p>	 <p>NTD32N06LT4 AMI Semiconductor / ON Semiconductor NTD32N06LT4 ON/</p>	 <p>NTD3808N-1G AMI Semiconductor / ON Semiconductor MOSFET N-CH 16V 12A IPAK</p>

heiße Teile

Mehr

NTD3055L104-1G	NTD3055L104G	NTD3055L104T4G	NTD3055L170	NTD3055L170-001
NTD3055L170-1G	NTD3055L170G	NTD3055L170T4	NTD3055L170T4G	NTD3055LT4G
NTD3055VLT4G	NTD30N02G	NTD30N02T4	NTD30N02T4G	NTD30N06RT4
NTD30N06T4G	NTD32N06-001	NTD32N06-1G	NTD32N06G	NTD32N06L
NTD32N06L-001	NTD32N06L-1G	NTD32N06LG	NTD32N06LT4G	NTD32N06T4G
NTD3813NT4G	NTD3817NT4G	NTD40N03R	NTD40N03R-1	NTD40N03R-1G
NTD40N03RG	NTD40N03RT4	NTD40N03RT4G	NTD4302-001	NTD4302-001G
NTD4302-1G	NTD4302G	NTD4302T4	NTD4302T4G	NTD4804N
NTD4804NT4G	NTD4805N	NTD4805N-1G	NTD4805NT4G	NTD4806N
NTD4806N-35G	NTD4806NA-35G	NTD4806NG	NTD4806NT4G	NTD4808N

Contact us: Info@Y-IC.com

HINZUFÜGEN: Einheit A5-B5 Nr.509, 5 / F Sing Win Fabrikgebäude, 15-17 Shing Yip St, Kwun Tong, Kowloon, HongKong.

Copyright © 2019 YIC International Co., Limited